

October 13, 2010 / Wednesday

13:30~ 14:55	Room 305
<i>Active-Matrix Devices</i>	
31. Oxide TFT III	

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| 13:30 ~ 13:55 | 31-1 | [Invited] How We Can Improve Characteristics and Stability of a-In-Ga-Zn-O Based TFTs
<i>K. Nomura, T. Kamiya, and H. Hosono (Tokyo Inst. of Tech., Japan)</i> |
| 13:55 ~ 14:15 | 31-2 | Role of Film Properties in Sub-Threshold Characteristics of Zinc Oxide Thin-Film Transistors (ZnO TFTs)
<i>Y. Kamada, S. Fujita (Kyoto Univ., Japan), T. Hiramatsu, T. Matsuda, M. Furuta, and T. Hirao (Kochi Univ. of Tech., Japan)</i> |
| 14:15 ~ 14:35 | 31-3 | Highly Stable IGZO TFT Performances with Inorganic Etch Stopper Layer for Diverse Electronic Displays
<i>C. W. Kim, J.-S. Heo, J. Kim, K.-S. Park, C.-D. Kim, Y. K. Hwang, I.-J. Chung (LG Display Co. Ltd, Korea), S. T. Meyers, and A. Grenville (Inpria Corp., USA)</i> |
| 14:35 ~ 14:55 | 31-4 | Photon-Enhanced Bias Instability of InGaZnO TFT with Dual Gate Structure
<i>M. Ryu, S.-H. Ko Park, C.-S. Hwang, S. M. Yoon, C. Byun, B. Kim, O.-S. Kwon, E.-S. Park, S. Yang, H. Oh, K. Kim, and K. I. Cho (ETRI, Korea)</i> |